

Amendments to the Claims:

This listing of claims replaces any and all prior claim lists.

Listing of Claims:

Claim 1 (currently amended). A method for manufacturing a compound semiconductor substrate, comprising the steps of:

- (a) epitaxially growing a compound semiconductor functional layer 2 on a substrate 1,
- (b) bonding a support substrate 3 to the compound semiconductor functional layer 2,
- (c) polishing the substrate 1 and a part of the compound semiconductor functional layer 2 on the side which is in contact with the substrate 1, to remove them,
- (d) bonding a thermally conductive substrate 4 having a thermal conductivity higher than that of the substrate 1 to the exposed surface of the compound semiconductor functional layer 2 which is provided in the step (c) to obtain a multilayer substrate and
- (d)(e) separating the support substrate 3 from the multilayer substrate.

Claim 2 (original). The method according to claim 1, wherein the compound semiconductor functional layer 2 includes at least two layers.

Claim 3 (currently amended). The method according to ~~claim 1 or 2~~ claim 1, wherein the compound semiconductor functional layer 2 includes at least one selected from the group

- consisting of In, Ga, and Al and at least one selected from the group consisting of N, P, As, and Sb.

Claim 4 (currently amended). The method according to ~~any one of claims 1 to 3~~ claim 1, wherein the thermally conductive substrate 4 includes at least one selected from the group consisting of Al, Cu, Fe, Mo, W, diamond, SiC, AlN, BN, and Si.

Claim 5 (original). A method for manufacturing a compound semiconductor substrate, comprising the steps of:

- (f) epitaxially growing a compound semiconductor functional layer 22 on a substrate 21,
- (g) bonding a thermally conductive substrate 23 having a thermal conductivity higher than that of the substrate 21 to the surface of the compound semiconductor functional layer 22 and
- (h) polishing the substrate 21 and a part of the compound semiconductor functional layer 22 on the side which is in contact with the substrate 21 to remove them.

Claim 6 (original). The method according to claim 5, wherein the compound semiconductor functional layer 2 includes at least two layers.

Claim 7 (currently amended). The method according to ~~claim 5 or 6~~ claim 5, wherein the compound semiconductor functional layer 2 includes at least one selected from the group

- consisting of In, Ga, and Al and at least one selected from the group consisting of N, P, As, and Sb.

Claim 8 (currently amended). The method according to ~~any one of claims 5 to 7~~ claim 5, wherein the thermally conductive substrate 23 includes at least one selected from the group consisting of Al, Cu, Fe, Mo, W, diamond, SiC, AlN, BN, and Si.

Claim 9 (currently amended). A method for manufacturing a electronic device, comprising the steps in the method according to ~~any one of claims 1 to 8~~ claim 1 and a step of forming an electrode on the resultant compound semiconductor substrate.